



NTE2076 Integrated Circuit 7-Segment Darlington Transistor Array w/Clamp Diode

Description:

The NTE2076 is constructed with a 7-circuit Darlington Transistor Array by a NPN Transistor and is a semi-conductor integrated circuit (IC) which can drive large electric current with very small input current.

Features:

- High Electric Voltage Endurance ($BV_{CEO} \geq 40V$)
- Large Electric Current Drive ($I_C (\max) = 150mA$)
- Convenient for Practical Attachment
- Available to Drive with PMOS IC Output
- Clamp Diode Attached
- Wide Input Voltage Range (-40V to +40V)
- Wide Operating Temperature Range ($T_A = -20^\circ$ to $+75^\circ C$)

Applications:

Attachment relay or printer drive, digit drive of LED and lamps indicator device, interface of MOS bipolar-logic IC, etc.

Absolute Maximum Ratings: ($T_A = -20^\circ$ to $+75^\circ C$ unless otherwise specified)

Voltage Between Collector and Emitter when Output is "High", V_{CEO}	-0.5 to +40V
Collector Current when Output is "Low", each Current for a Circuit, I_C	150mA
Input Voltage, V_i	-40 to +40V
Clamp Diode Positive-Direction Current, I_r	150mA
Clamp Diode Negative-Direction Voltage, V_a	40V
Power Consumption ($T_A = +25^\circ C$), P_d	1.47W
Operating Ambient Temperature Range, T_{opr}	-20° to +75°C
Storage Temperature Range, T_{stg}	-55° to +125°C

Electrical Characteristics: ($T_A = -20^\circ$ to $+75^\circ C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Output Voltage	V_O		0	-	40	V
Collector Current	I_C	Duty Cycle 40% or less (each current for a circuit)	0	-	150	mA
"High" Input Voltage	$V^{“H”}$	$I_C = 150mA$	7	-	35	V
"Low" Input Voltage	$V^{“L”}$	$I_{O(Leak)} = 50\mu A$	0	-	1	V

Pin Connection Diagram

